

Edmundo A Gutiérrez-D

List of Publications by Year in descending order

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Version: 2024-02-01

30
papers

60
citations

1937632

4
h-index

1720014

7
g-index

31
all docs

31
docs citations

31
times ranked

70
citing authors

#	ARTICLE	IF	CITATIONS
1	Self-Heating Effect in a 65 nm MOSFET at Cryogenic Temperatures. IEEE Transactions on Electron Devices, 2022, 69, 900-904.	3.0	8
2	Editorial Kudos to Our Reviewers. IEEE Transactions on Device and Materials Reliability, 2021, 21, 454-454.	2.0	0
3	DC and 28 GHz Reliability of a SOI FET Technology. IEEE Journal of the Electron Devices Society, 2020, 8, 385-390.	2.1	1
4	Stress- and Trap-Induced Body Fluctuations in 45nm SOI MOSFETs. , 2020, , .		0
5	Systematic Characterization of Random Telegraph Noise and Its Dependence with Magnetic Fields in MOSFET Devices. , 2020, , 135-174.		2
6	Editorial From Edmundo A. Gutiérrez-D. IEEE Transactions on Device and Materials Reliability, 2020, 20, 3-3.	2.0	0
7	Editorial for December 2020. IEEE Transactions on Device and Materials Reliability, 2020, 20, 631-631.	2.0	0
8	Editorial Kudos to Our Reviewers. IEEE Transactions on Device and Materials Reliability, 2020, 20, 630-630.	2.0	0
9	RF and DC degradation of a SOI FET technology. , 2019, , .		0
10	Experimental Characterization of the Random Telegraph Noise Signature in MOSFETs Under the Influence of Magnetic Fields. IEEE Electron Device Letters, 2018, 39, 1054-1057.	3.9	2
11	The semiconductor device technology and its societal impact. , 2016, , 349-412.		0
12	The silicon era and beyond. , 2016, , 413-441.		0
13	Thermo-Magnetic Effects in Nano-Scaled MOSFET: An Experimental, Modeling, and Simulation Approach. IEEE Journal of the Electron Devices Society, 2015, 3, 78-84.	2.1	1
14	Improved Detection of Magnetic Signals by a MEMS Sensor Using Stochastic Resonance. PLoS ONE, 2014, 9, e109534.	2.5	5
15	Impact of hot carrier degradation on MOSFET small-signal input, output, and transmission features. , 2014, , .		1
16	Non-homogeneous space mechanical strain induces asymmetrical magneto-tunneling conductance in MOSFETs. , 2014, , .		2
17	Identifying the Diffusion and Drift Conduction Regions in MOSFETs Through \$\$\$-Parameters. IEEE Transactions on Electron Devices, 2013, 60, 1288-1291.	3.0	0
18	Respiratory Magnetogram Detected with a MEMS Device. International Journal of Medical Sciences, 2013, 10, 1445-1450.	2.5	11

#	ARTICLE	IF	CITATIONS
19	Experimental evidence of unconventional room-temperature Quantum Hall effect (RTQHE) in 65nm Si nMOSFETs at very low magnetic fields. , 2010, , .		1
20	Gate current tunneling modulated by magnetic field in 65nm nMOSFET's. , 2009, , .		0
21	Analysis of the impact of the drain-junction tunneling effect on a microwave MOSFET from S-parameter measurements. Solid-State Electronics, 2009, 53, 145-149.	1.4	0
22	Magnetic field induced gate leakage current in 65nm nMOS transistors. , 2009, , .		1
23	ANALYTICAL CHARACTERIZATION AND MODELING OF SHIELDED TEST STRUCTURES FOR RF-CMOS. International Journal of High Speed Electronics and Systems, 2008, 18, 793-803.	0.7	2
24	Electron diffusion in 0.18 μm MOS transistors at 200 $^{\circ}\text{C}$. , 2008, , .		0
25	RF magnetic emission and electrical coupling in silicon integrated circuits. , 2008, , .		4
26	Numerical simulations of propagation of SCWs in strained Si/SiGe heterostructures at 4.2 and 77 K. Journal of Computational Electronics, 2007, 6, 137-140.	2.5	1
27	Temperature dependence of the 2D electron transport in Si accumulation layers. , 2006, , .		0
28	Selfheating effects in silicon resistors operated at cryogenic ambient temperatures. Solid-State Electronics, 1993, 36, 41-52.	1.4	14
29	Experimental determination of selfheating in silicon resistors operated at cryogenic temperatures. Microelectronic Engineering, 1992, 19, 865-868.	2.4	1
30	Transconductance degradation and its correlation to the second substrate current hump of submicron NMOS LDD transistors. Microelectronic Engineering, 1991, 15, 449-452.	2.4	3